



# STI360N4F6, STP360N4F6

N-channel 40 V, 120 A STripFET™ VI DeepGATE™  
Power MOSFET in I<sup>2</sup>PAK and TO-220 packages

Datasheet – preliminary data

## Features

Order codes	V <sub>DSS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub>
STI360N4F6	40 V	< 1.8 mΩ	120 A <sup>(1)</sup>
STP360N4F6			

- 1. Current limited by package
- Low gate charge
- Very low on-resistance
- High avalanche ruggedness

## Applications

- Switching applications

## Description

These devices are N-channel Power MOSFETs developed using the 6th generation of STripFET™ DeepGATE™ technology, with a new gate structure. The resulting Power MOSFETs exhibit the lowest R<sub>DS(on)</sub> in all packages.

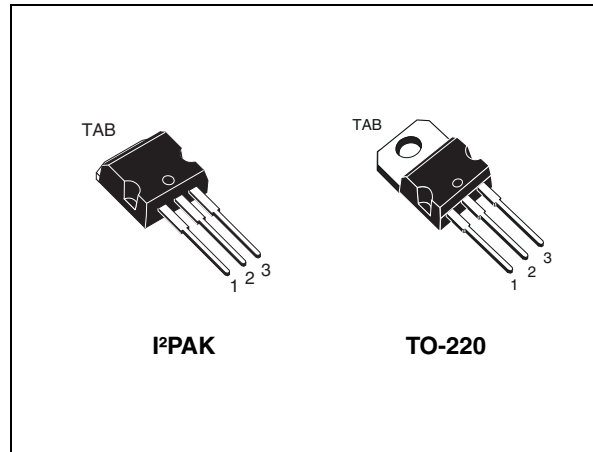


Figure 1. Internal schematic diagram

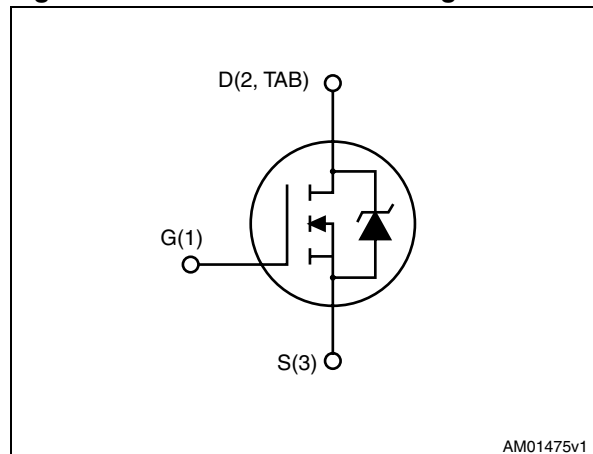


Table 1. Device summary

Order codes	Marking	Package	Packaging
STI360N4F6	360N4F6	I <sup>2</sup> PAK	Tube
STP360N4F6		TO-220	

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage	40	V
$V_{GS}$	Gate-source voltage	$\pm 20$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	120	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	120	A
$I_{DM}^{(1)}$	Drain current (pulsed)	480	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	300	W
	Derating factor	2	W/ $^\circ\text{C}$
$T_{stg}$	Storage temperature	- 55 to 175	$^\circ\text{C}$
$T_j$	Operating junction temperature		

1. Current limited by package

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	0.5	$^\circ\text{C}/\text{W}$
$R_{thj-a}$	Thermal resistance junction-ambient max	62.5	$^\circ\text{C}/\text{W}$
$T_l$	Maximum lead temperature for soldering purpose	300	$^\circ\text{C}$

## 2 Electrical characteristics

( $T_{CASE} = 25\text{ °C}$  unless otherwise specified)

**Table 4. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage ( $V_{GS} = 0$ )	$I_D = 250\ \mu A$	40			V
$I_{DSS}$	Zero gate voltage Drain current ( $V_{GS} = 0$ )	$V_{DS} = 40\text{ V}$ $V_{DS} = 40\text{ V}, T_C = 125\text{ °C}$			1 100	$\mu A$ $\mu A$
$I_{GSS}$	Gate-body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu A$	3		4.5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 60\text{ A}$		TBD	1.8	m $\Omega$

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance			17930		pF
$C_{oss}$	Output capacitance	$V_{DS} = 25\text{ V}, f = 1\text{ MHz},$ $V_{GS} = 0$	-	1560	-	pF
$C_{rss}$	Reverse transfer capacitance			1170		pF
$Q_g$	Total gate charge			340		nC
$Q_{gs}$	Gate-source charge	$V_{DD} = 20\text{ V}, I_D = 120\text{ A},$ $V_{GS} = 10\text{ V}$	-	TBD	-	nC
$Q_{gd}$	Gate-drain charge			TBD		nC

**Table 6. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on delay time Rise time	$V_{DD} = 20\text{ V}, I_D = 60\text{ A}$ $R_G = 4.7\ \Omega, V_{GS} = 10\text{ V}$	-	TBD	-	ns
$t_{d(off)}$ $t_f$	Turn-off-delay time Fall time		-	TBD	-	ns

**Table 7. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
$I_{SD}^{(1)}$	Source-drain current		-		120	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		480	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 120 \text{ A}, V_{GS} = 0$	-		1.1	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 120 \text{ A}, V_{DD} = 32 \text{ V}$ $di/dt = 100 \text{ A}/\mu\text{s},$ $T_j = 150 \text{ }^\circ\text{C}$	-	TBD		ns
$Q_{rr}$	Reverse recovery charge					nC
$I_{RRM}$	Reverse recovery current					A

1. Current limited by package
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

### 3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

**Table 8. I<sup>2</sup>PAK (TO-262) mechanical data**

DIM.	mm.		
	min.	typ	max.
A	4.40		4.60
A1	2.40		2.72
b	0.61		0.88
b1	1.14		1.70
c	0.49		0.70
c2	1.23		1.32
D	8.95		9.35
e	2.40		2.70
e1	4.95		5.15
E	10		10.40
L	13		14
L1	3.50		3.93
L2	1.27		1.40

Figure 2. I<sup>2</sup>PAK (TO-262) drawing

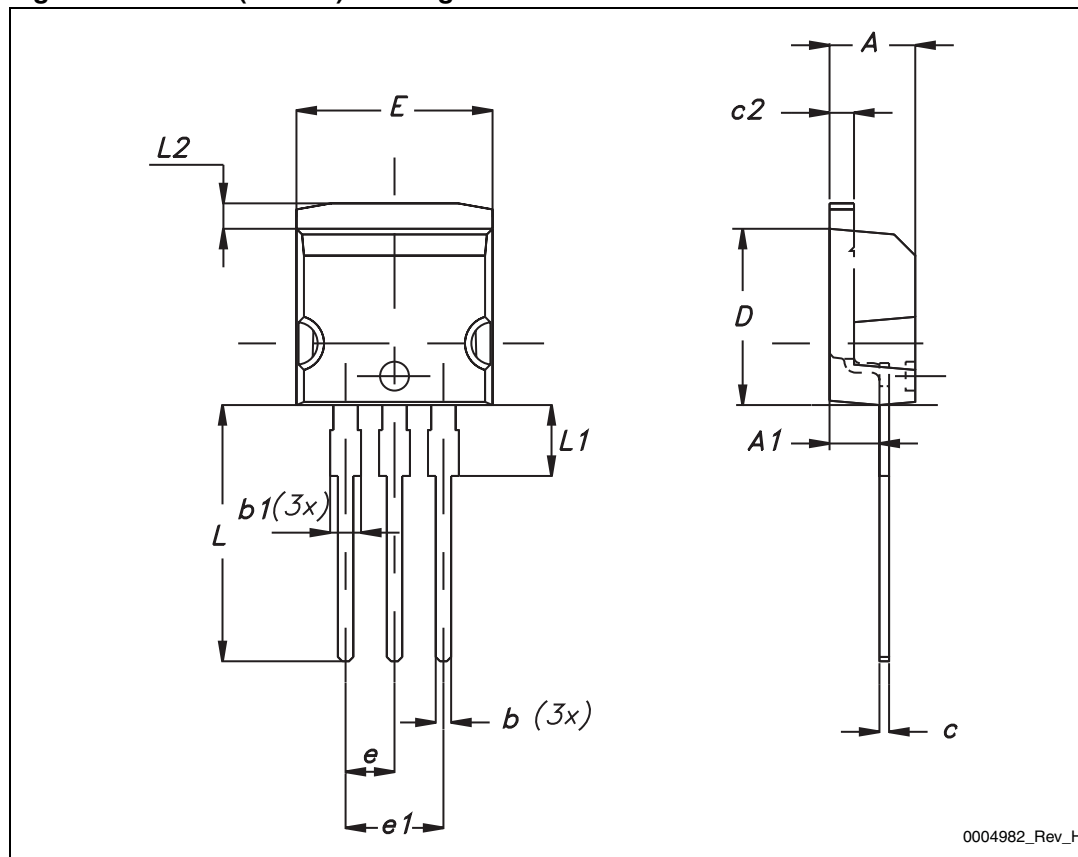
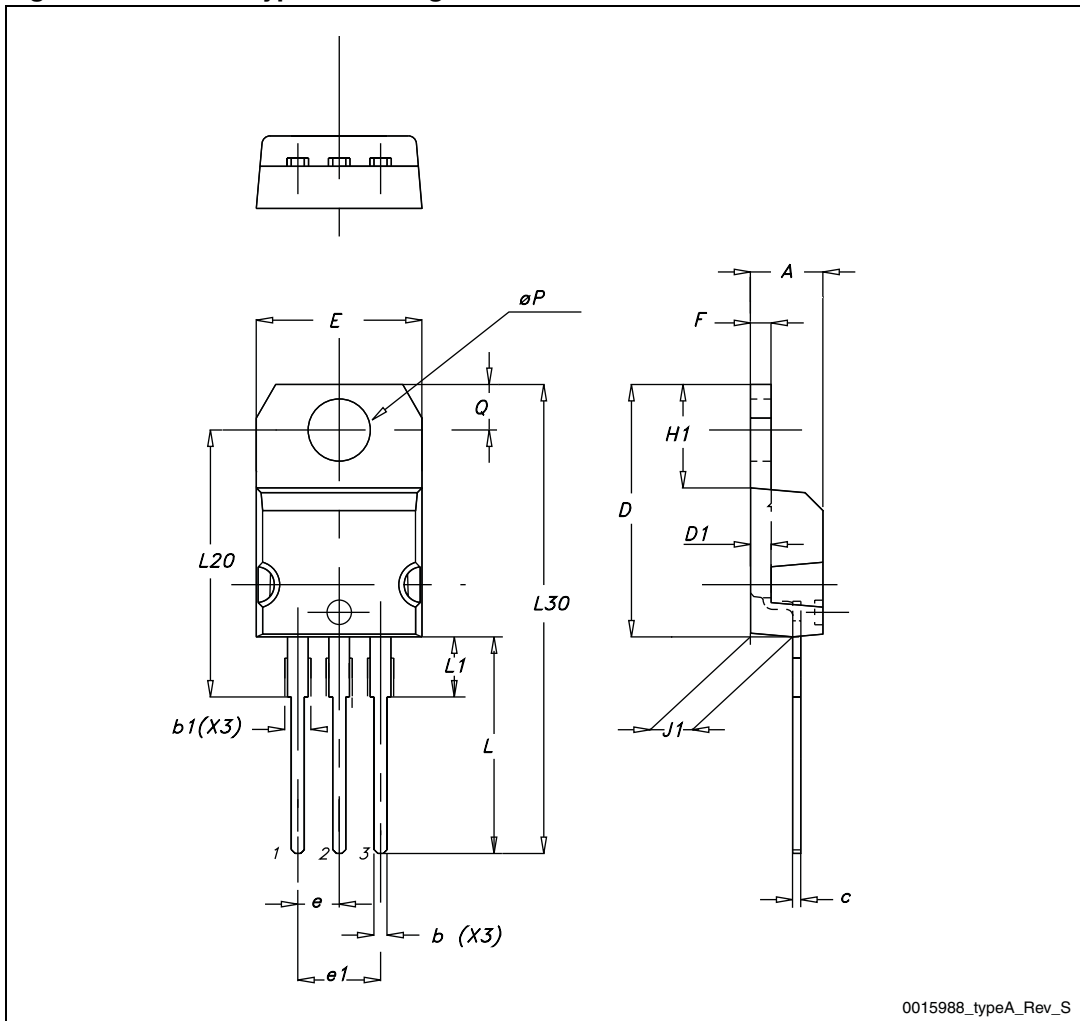


Table 9. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95



Figure 3. TO-220 type A drawing



## 4 Revision history

Table 10. Document revision history

Date	Revision	Changes
08-Aug-2012	1	Initial release.

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